Yang Shao

List of Publications by Year
in descending order

26 papers	265 citations	1040056 9 h-index	1125743 13 g-index
26 all docs	26 docs citations	26 times ranked	387 citing authors

#	Article	IF	Citations
1	Low-Voltage a-InGaZnO Thin-Film Transistors With Anodized Thin HfO₂ Gate Dielectric. IEEE Electron Device Letters, 2015, 36, 573-575.	3.9	51
2	Anodized ITO Thinâ€Film Transistors. Advanced Functional Materials, 2014, 24, 4170-4175.	14.9	41
3	Oxygen Interstitial Creation in a-IGZO Thin-Film Transistors Under Positive Gate-Bias Stress. IEEE Electron Device Letters, 2017, 38, 1252-1255.	3.9	41
4	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. ACS Applied Materials & Interfaces, 2018, 10, 25850-25857.	8.0	36
5	Amorphous Indium Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Technique. IEEE Transactions on Electron Devices, 2016, 63, 1072-1077.	3.0	18
6	A Back-Channel-Etched Amorphous InGaZnO Thin-Film Transistor Technology With Al-Doped ZnO as Source/Drain and Pixel Electrodes. IEEE Transactions on Electron Devices, 2016, 63, 2205-2209.	3.0	15
7	Indiumâ€“Tinâ€“Oxide Thin-Film Transistors With In Situ Anodized Ta₂O₅Passivation Layer. IEEE Electron Device Letters, 2016, 37, 603-606.	3.9	12
8	Back Channel Anodization Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors Process. IEEE Electron Device Letters, 2015, 36, 357-359.	3.9	9
9	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	2.1	9
10	Homo-Junction Bottom-Gate Amorphous Inâ€“Gaâ€“Znâ€“O TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	2.1	9
11	Pâ€9: Parylene / Al₂O₃ Double Layer Passivated Amorphous InGaZnO Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1258-1261.	0.3	7
12	Fabrication of p-type copper oxide thin-film transisters at different oxygen partial pressure. , 2014, , .		6
13	A Multi-$V_{mathrm {th}}$ a-IGZO TFT Technology Using Anodization to Selectively Reduce Oxygen Vacancy Concentration in Channel Regions. IEEE Electron Device Letters, 2014, 35, 1248-1250.	3.9	3
14	Characteristics of double-gate a-IGZO TFT. , 2014, , .		2
15	Pâ€6.1: Asymmetric Effects of Gateâ€Bias Stress Voltage on the Stability under Positive and Negative Gateâ€Bias Stress of aâ€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 597-600.	0.3	2
16	Impacts of substrate heating schemes on characteristics of amorphous indium-gallium-zinc-oxide (a-IGZO) TFTs fabricated on flexible substrates. , 2014, , .		1
17	Impact of sputtering power of source/drain metal on performances of a-IGZO thin film transistors fabricated using wet back-channel-etch process. , 2017, , .		1
18	ZnSnO thin-film transistors by reactive co-sputtering of Zn and Sn metal targets. , 2017, , .		1

#	Article	IF	Citations
19	Dynamic Threshold Voltage Modulation in Double-Gate Indium-Gallium-Zinc Oxide Thin-Film Transistors: Influence of the Active Layer Thickness. , 2018, , .		1
20	Homojunction In<inf>2</inf>O<inf>3</inf>-TFTs prepared by anodization technique. , 2014, , .		0
21	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
22	Electron-transport layer free perovskite solar cells with anodized ITO electrode. , 2017, , .		0
23	Ti Film Thickness Influences on the Back Channel Etched Amorphous InGaZnO<inf>4</inf> Thin Film Transistors. , 2018, , .		0
24	24.5: Backâ€Channelâ€Etched aâ€IGZO TFTs with TiO₂:Nb Protective Layer. Digest of Technical Papers SID International Symposium, 2018, 49, 263-266.	0.3	0
25	Systematic Defect Manipulation in Metal Oxide Semiconductors towards High-Performance Thin-Film Transistors. , 2020, , .		0
26	Fully Self-Aligned Homojunction Bottom-Gate Amorphous InGaZnO TFTs with Al Reacted Source/Drain Regions. , 2020, , .		0